

REMARKS

Claims 45-64 are pending in this application, with claims 45-50 being independent. Claims 45-50 have been amended. No new matter has been added.

Figs. 1D and 2A-2D have been amended in response to the objection to the drawings. Support for the amendment to Fig. 1D (replacing erroneous reference numeral 108 with correct reference numeral 104) may be found in Fig. 1E (showing the film 104 positioned on top of the active layer 107) and at page 15, lines 2-8 (stating that the film 104 is positioned on top of the active layer 107). Support for the current and prior amendments to Figs. 2A-2D may be found in Fig. 1E (showing the film 104 positioned on top of the active layer 107) and at page 15, lines 7-8 and 18-21 (stating that the gate-insulating film 110 includes the film 104 and the film 109). No new matter has been added.

In response to the objection to the amendment filed 6/20/02 as adding new matter with respect to the gate electrode over the gate insulating film and the first insulating film having a side aligned with a side of the crystalline semiconductor island, applicant respectfully submits that these elements do not constitute new matter. In particular, Fig. 1E clearly shows the first insulating film 104 having a side aligned with a side of the crystalline semiconductor island corresponding to the active layer 107. In addition, the application notes at page 15, lines 2-5, that the silicon film 106 is etched to form the island while leaving the film 104 on the silicon film 106. Thus, since the edges of the film 104 and the active layer 107 are formed by the same etching process, it is not surprising that the edges are aligned as shown in Fig. 1E.

Fig. 2A shows a gate electrode 111 over the gate insulating film 110. As noted at page 15, lines 18-22, the gate insulating film 110 includes the first insulating film 104 and the second

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insulating film over a crystalline semiconductor island and a second insulating film over the first insulating film, with the first insulating film having a side aligned with a side of the crystalline semiconductor island and the second insulating film extending beyond an edge of the first insulating film, as recited in each of the independent claims.

Enclosed is a check in the amount of \$860 for the Request for Continued Examination Fee and the Petition for Extension of Time fee. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

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